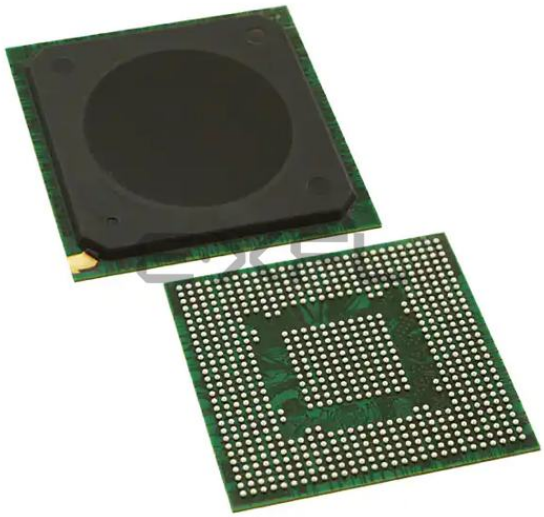

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300c4s
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	Security; SEC 3.0
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (2)
USB	USB 2.0 + PHY (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 125°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	689-BBGA Exposed Pad
Supplier Device Package	689-TEPBGA II (31x31)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8377evragd

There are two I^2C controllers. These synchronous, multi-master buses can be connected to additional devices for expansion and system development.

The DUART supports full-duplex operation and is compatible with the PC16450 and PC16550 programming models. 16-byte FIFOs are supported for both the transmitter and the receiver.

The main component of the enhanced local bus controller (eLBC) is its memory controller, which provides a seamless interface to many types of memory devices and peripherals. The memory controller is responsible for controlling eight memory banks shared by a NAND Flash control machine (FCM), a general-purpose chip-select machine (GPCM), and up to three user-programmable machines (UPMs). As such, it supports a minimal glue logic interface to SRAM, EPROM, NOR Flash EPROM, NAND Flash, EPROM, burstable RAM, regular DRAM devices, extended data output DRAM devices, and other peripherals. The eLBC external address latch enable (LALE) signal allows multiplexing of addresses with data signals to reduce the device pin count.

The enhanced local bus controller also includes a number of data checking and protection features, such as data parity generation and checking, write protection, and a bus monitor to ensure that each bus cycle is terminated within a user-specified period. The local bus can operate at up to 133 MHz.

The system timers include the following features: periodic interrupt timer, real time clock, software watchdog timer, and two general-purpose timer blocks.

1.8 Security Engine

The optional security engine is optimized to handle all the algorithms associated with IPSec, IEEE 802.11i, and iSCSI. The security engine contains one crypto-channel, a controller, and a set of crypto execution units (EUs). The execution units are as follows:

- Data encryption standard execution unit (DEU), supporting DES and 3DES
- Advanced encryption standard unit (AESU), supporting AES
- Message digest execution unit (MDEU), supporting MD5, SHA1, SHA-256, and HMAC with any algorithm
- One crypto-channel supporting multi-command descriptor chains

1.9 PCI Controller

The PCI controller includes the following features:

- *PCI Specification Revision 2.3* compatible
- Single 32-bit data PCI interface operates at up to 66 MHz
- PCI 3.3-V compatible (not 5-V compatible)
- Support for host and agent modes
- On-chip arbitration, supporting 5 external masters on PCI
- Selectable hardware-enforced coherency

1.12 Enhanced Secured Digital Host Controller (eSDHC)

The enhanced SD host controller (eSDHC) has the following features:

- Conforms to *SD Host Controller Standard Specification, Rev 2.0* with Test Event register support.
- Compatible with the *MMC System Specification, Rev 4.0*
- Compatible with the *SD Memory Card Specification, Rev 2.0*, and supports High Capacity SD memory cards
- Compatible with the *SDIO Card Specification Rev, 1.2*
- Designed to work with SD Memory, miniSD Memory, SDIO, miniSDIO, SD Combo, MMC, MMC*plus*, MMC 4x, and RS-MMC cards
- SD bus clock frequency up to 50 MHz
- Supports 1-/4-bit SD and SDIO modes, 1-/4-bit MMC modes
- Supports internal DMA capabilities

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the chip. The device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

This table provides the absolute maximum ratings.

Table 2. Absolute Maximum Ratings[1]

Characteristic	Symbol	Max Value	Unit	Note
Core supply voltage	V_{DD}	–0.3 to 1.1	V	—
PLL supply voltage (e300 core, eLBC, and system)	AV_{DD}	–0.3 to 1.1	V	—
DDR1 and DDR2 DRAM I/O voltage	GV_{DD}	–0.3 to 2.75 –0.3 to 1.98	V	—
Three-speed Ethernet I/O, MII management voltage	LV_{DD}[1,2]	–0.3 to 3.63	V	—
PCI, DUART, system control and power management, I^2C, and JTAG I/O voltage	OV_{DD}	–0.3 to 3.63	V	—
Local bus	LBV_{DD}	–0.3 to 3.63	V	—
SerDes	L[1,2]_nV_{DD}	–0.3 to 1.1	V	6

Table 2. Absolute Maximum Ratings[1] (continued)

Characteristic		Symbol	Max Value	Unit	Note
Input voltage	DDR DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2, 4
	DDR DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2, 4
	Three-speed Ethernet signals	LV_{IN}	–0.3 to (LV_{DD} + 0.3)	V	—
	PCI, DUART, CLKIN, system control and power management, I^2C, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	3, 4, 5
	Local Bus	LB_{IN}	–0.3 to (LBV_{DD} + 0.3)	V	—
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:
1. Functional and tested operating conditions are given in Table 3. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
4. (M,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.
5. Overshoot/undershoot by OV_{IN} on the PCI interface does not comply to the *PCI Electrical Specification* for 3.3-V operation, as shown in Figure 2.
6. L[1,2]_$n$$V_{DD}$ includes $SDAV_{DD\_0}$, $XCOREV_{DD}$, and $XPADV_{DD}$ power inputs.

2.1.2 Power Supply Voltage Specification

This table provides recommended operating conditions for the device. Note that the values in this table are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 3. Recommended Operating Conditions

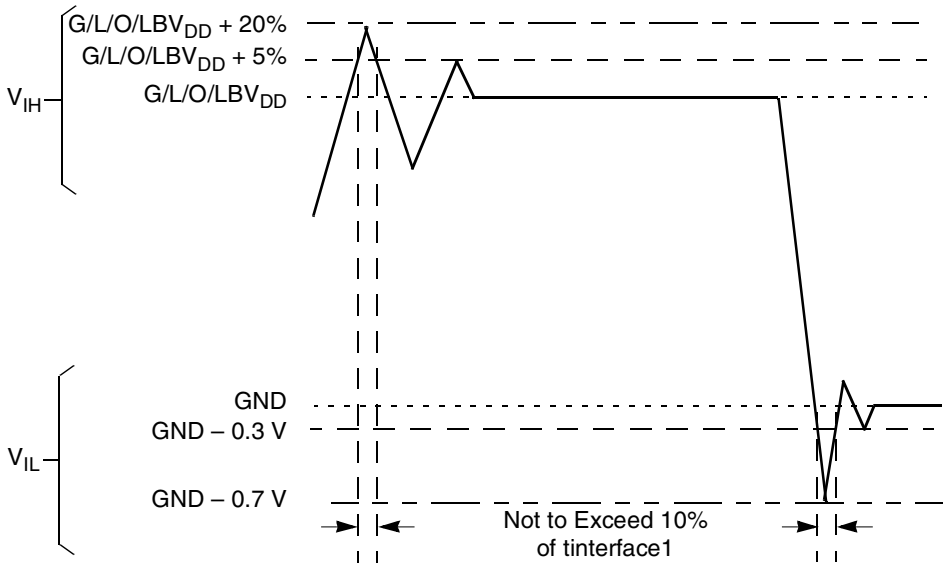
Characteristic		Symbol	Recommended Value	Unit	Note
Core supply voltage	up to 667 MHz	V_{DD}	1.0 ± 50 mV	V	1
	800 MHz		1.05 ± 50 mV	V	1
PLL supply voltage (e300 core, eLBC and system)	up to 667 MHz	AV_{DD}	1.0 ± 50 mV	V	1, 2
	800 MHz		1.05 ± 50 mV	V	1, 2
DDR1 and DDR2 DRAM I/O voltage		GV_{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	1
Three-speed Ethernet I/O, MII management voltage		LV_{DD}[1,2]	3.3 V ± 165 mV 2.5 V ± 125 mV	V	—
PCI, local bus, DUART, system control and power management, I^2C, and JTAG I/O voltage		OV_{DD}	3.3 V ± 165 mV	V	1
Local Bus		LBV_{DD}	1.8 V ± 90 mV 2.5 V ± 125 mV 3.3 V ± 165 mV	V	—

Table 3. Recommended Operating Conditions (continued)

Characteristic		Symbol	Recommended Value	Unit	Note
SerDes	up to 667 MHz	L[1,2]_nV_{DD}	1.0 ± 50 mV	V	1, 3
	800 MHz		1.05 V ± 50 mV	V	1, 3
Operating temperature range	commerical	T_a T_j	T_a=0 (min)— T_j=125 (max)	°C	—
	extended temperature	T_a T_j	T_a=–40 (min)— T_j=125 (max)	°C	—

Notes:
1. GV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.
2. AV_{DD} is the input to the filter discussed in Section 25.1, "PLL Power Supply Filtering," and is not necessarily the voltage at the AVDD pin.
3. L[1,2]_nV_{DD}, $SDAV_{DD\_0}$, $XCOREV_{DD}$, and $XPADV_{DD}$ power inputs.

This figure shows the undershoot and overshoot voltages at the interfaces of the device.



Note:
1. Note that $t_{interface}$ refers to the clock period associated with the bus clock interface.
2. Note that with the PCI overshoot allowed (as specified above), the device does not fully comply with the maximum AC ratings and device protection guideline outlined in the *PCI Rev. 2.3 Specification* (Section 4.2.2.3).

Figure 2. Overshoot/Undershoot Voltage for GV_{DD}/LV_{DD}/OV_{DD}/LBV_{DD}

Table 22. DUART DC Electrical Characteristics (continued)

Parameter	Symbol	Min	Max	Unit
Low-level output voltage, I_{OL} = 100 µA	V_{OL}	—	0.2	V
Input current, (0 V ≤V_{IN} ≤ OV_{DD})	I_{IN}	—	±30	µA

Note: The symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 2.

7.2 DUART AC Electrical Specifications

this table provides the AC timing parameters for the DUART interface of the device.

Table 23. DUART AC Timing Specifications

Parameter	Value	Unit	Note
Minimum baud rate	256	baud	—
Maximum baud rate	> 1,000,000	baud	1
Oversample rate	16	—	2

Notes:
1. Actual attainable baud rate will be limited by the latency of interrupt processing.
2. The middle of a start bit is detected as the 8^{th} sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16^{th} sample.

8 Ethernet: Enhanced Three-Speed Ethernet (eTSEC)

This section provides the AC and DC electrical characteristics for the enhanced three-speed Ethernet controller.

8.1 Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1000 Mbps)—MII/RGMII/RTBI/RMII DC Electrical Characteristics

The electrical characteristics specified here apply to media independent interface (MII), reduced gigabit media independent interface (RGMII), reduced ten-bit interface (RTBI), reduced media independent interface (RMII) signals, management data input/output (MDIO) and management data clock (MDC).

The MII and RMII interfaces are defined for 3.3 V, while the RGMII and RTBI interfaces can be operated at 2.5 V. The RGMII and RTBI interfaces follow the *Reduced Gigabit Media-Independent Interface (RGMII) Specification Version 1.3*. The RMII interface follows the *RMII Consortium RMII Specification Version 1.2*.

8.2.1.2 MII Receive AC Timing Specifications

This table provides the MII receive AC timing specifications.

Table 27. MII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V ± 5%.

Parameter	Symbol[1]	Min	Typical	Max	Unit
Input low voltage	V_{IL}	—	—	0.7	V
Input high voltage	V_{IH}	1.9	—	—	V
RX_CLK clock period 10 Mbps	t_{MRX}	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise time (20%–80%)	t_{MRXR}	1.0	—	4.0	ns
RX_CLK clock fall time (80%–20%)	t_{MRXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure provides the AC test load for eTSEC.

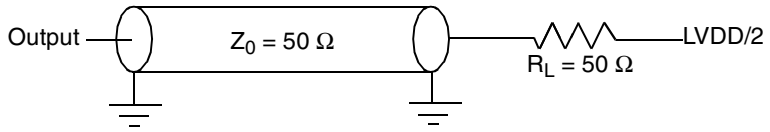


Figure 8. eTSEC AC Test Load

Table 32. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Conditions		Symbol	Min	Max	Unit
Supply voltage (3.3 V)	—		LV_{DD1}	3.135	3.465	V
Output high voltage	I_{OH} = –1.0 mA	LV_{DD1} = Min	V_{OH}	2.10	LV_{DD1} + 0.3	V
Output low voltage	I_{OL} = 1.0 mA	LV_{DD1} = Min	V_{OL}	GND	0.50	V
Input high voltage	—		V_{IH}	2.00	—	V
Input low voltage	—		V_{IL}	—	0.80	V
Input high current	LV_{DD1} = Max	V_{IN} [1] = 2.1 V	I_{IH}	—	30	μA
Input low current	LV_{DD1} = Max	V_{IN} = 0.5 V	I_{IL}	–600	—	μA

8.3.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 33. MII Management AC Timing Specifications

Parameter	Symbol[1]	Min	Typical	Max	Unit	Note
MDC frequency	f_{MDC}	—	2.5	—	MHz	2
MDC period	t_{MDC}	80	—	400	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO valid	t_{MDKHDV}	$2 \times (t_{plb\_clk} \times 8)$	—	—	ns	4
MDC to MDIO delay	t_{MDKHDX}	10	—	$2 \times (t_{plb\_clk} \times 8)$	ns	2, 4
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time (20%–80%)	t_{MDCR}	—	—	10	ns	3
MDC fall time (80%–20%)	t_{MDCF}	—	—	10	ns	3

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the system clock speed.
3. Guaranteed by design.
4. t_{plb_clk} is the platform (CSB) clock divided according to the SCCR[TSEC1CM].

Table 38. Local Bus DC Electrical Characteristics (LBV_{DD} = 1.8 V)

At recommended operating conditions with LBV_{DD} = 1.8 V.

Parameter	Conditions		Symbol	Min	Max	Unit
Supply voltage 1.8 V	—		LBV_{DD}	1.71	1.89	V
Output high voltage	I_{OH} = –1.0 mA	LBV_{DD} = Min	V_{OH}	LBV_{DD} – 0.45	—	V
Output low voltage	I_{OL} = 1.0 mA	LBV_{DD} = Min	V_{OL}	—	0.45	V
Input high voltage	—	LBV_{DD} = Min	V_{IH}	0.65 × LBV_{DD}	LBV_{DD} + 0.3	V
Input low voltage	—	LBV_{DD} = Min	V_{IL}	–0.3	0.35 × LBV_{DD}	V
Input high current	V_{IN} [1] = LBV_{DD}		I_{IH}	—	10	μA
Input low current	V_{IN} [1] = GND		I_{IL}	–10	—	μA

10.2 Local Bus AC Electrical Specifications

This table describes the general timing parameters of the local bus interface of the device when in PLL enable mode.

Table 39. Local Bus General Timing Parameters—PLL Enable Mode

Parameter	Symbol[1]	Min	Max	Unit	Note
Local bus cycle time	t_{LBK}	7.5	15	ns	2
Input setup to local bus clock (except LUPWAIT/$\overline{\text{LGTA}}$)	t_{LBIVKH}	1.5	—	ns	3, 4
Input hold from local bus clock	t_{LBIXKH}	1.0	—	ns	3, 4
LUPWAIT/$\overline{\text{LGTA}}$ input setup to local bus clock	$t_{LBIVKH1}$	1.5	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock to LALE rise	t_{LBKHLR}	—	4.5	ns	—
Local bus clock to output valid (except LALE)	t_{LBKHOV}	—	4.5	ns	3

Table 39. Local Bus General Timing Parameters—PLL Enable Mode (continued)

Parameter	Symbol[1]	Min	Max	Unit	Note
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	3.8	ns	3, 8
Output hold from local bus clock for LAD/LDP	t_{LBKHOX}	1	—	ns	3

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to rising edge of LSYNC_IN at $LBV_{DD}/2$ and the $0.4 \times LBV_{DD}$ of the signal in question.
3. All signals are measured from $LBV_{DD}/2$ of the rising/falling edge of LSYNC_IN to $0.5 \times LBV_{DD}$ of the signal in question.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when LBCR[AHD] is set and the load on LALE output pin is at least 10pF less than the load on LAD output pins.
6. $t_{LBOTOT2}$ should be used when LBCR[AHD] is not set and the load on LALE output pin is at least 10pF less than the load on LAD output pins.
7. $t_{LBOTOT3}$ should be used when LBCR[AHD] is not set and the load on LALE output pin equals to the load on LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

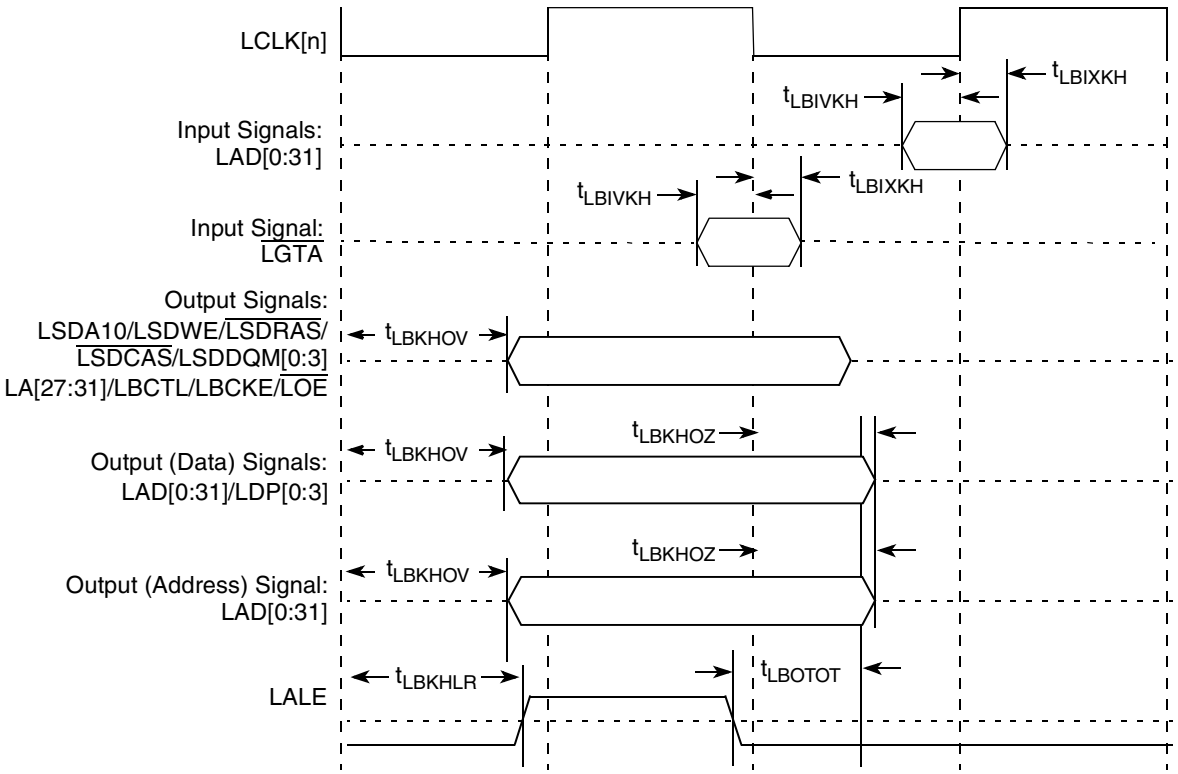


Figure 21. Local Bus Signals, Non-special Signals Only (PLL Bypass Mode)

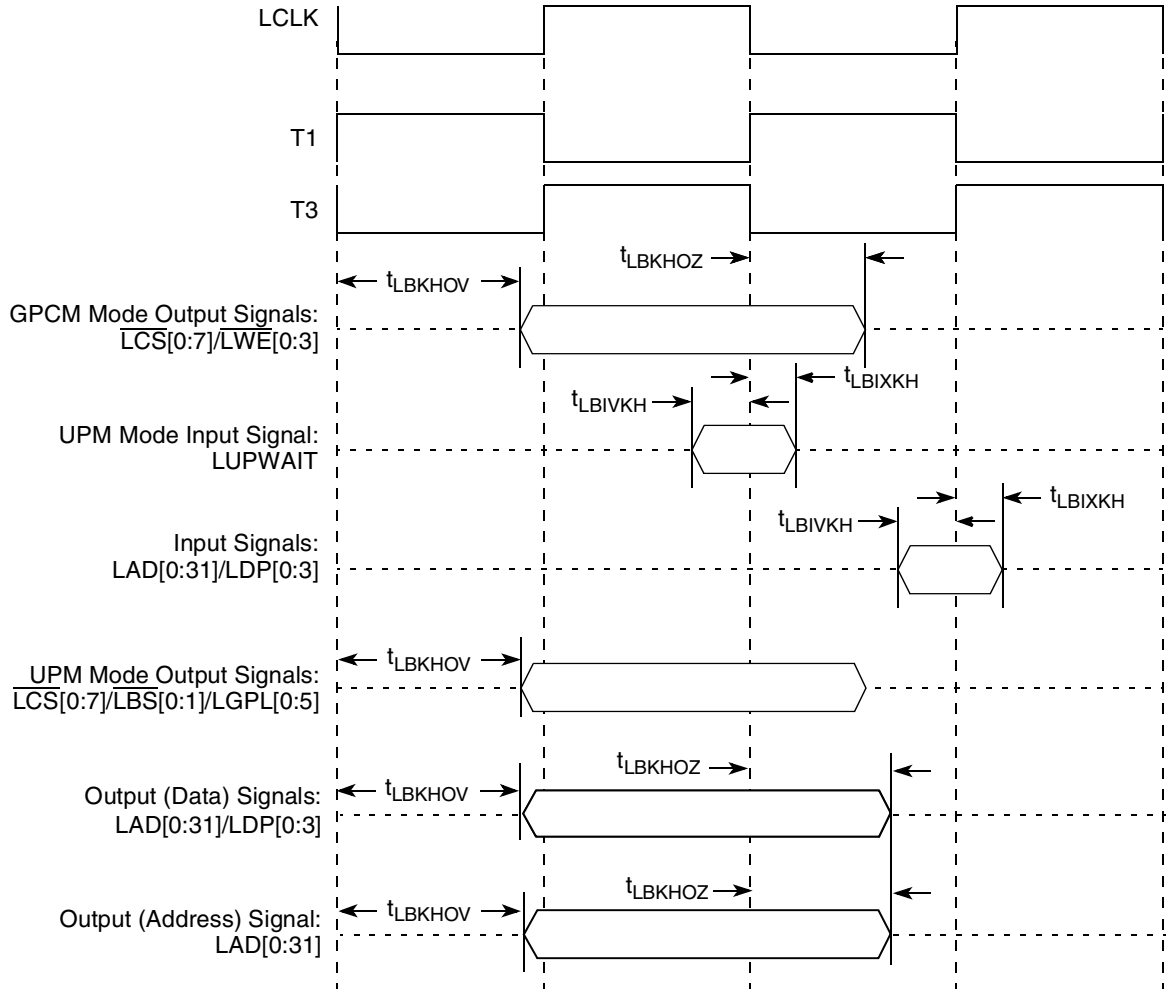


Figure 23. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (PLL Bypass Mode)

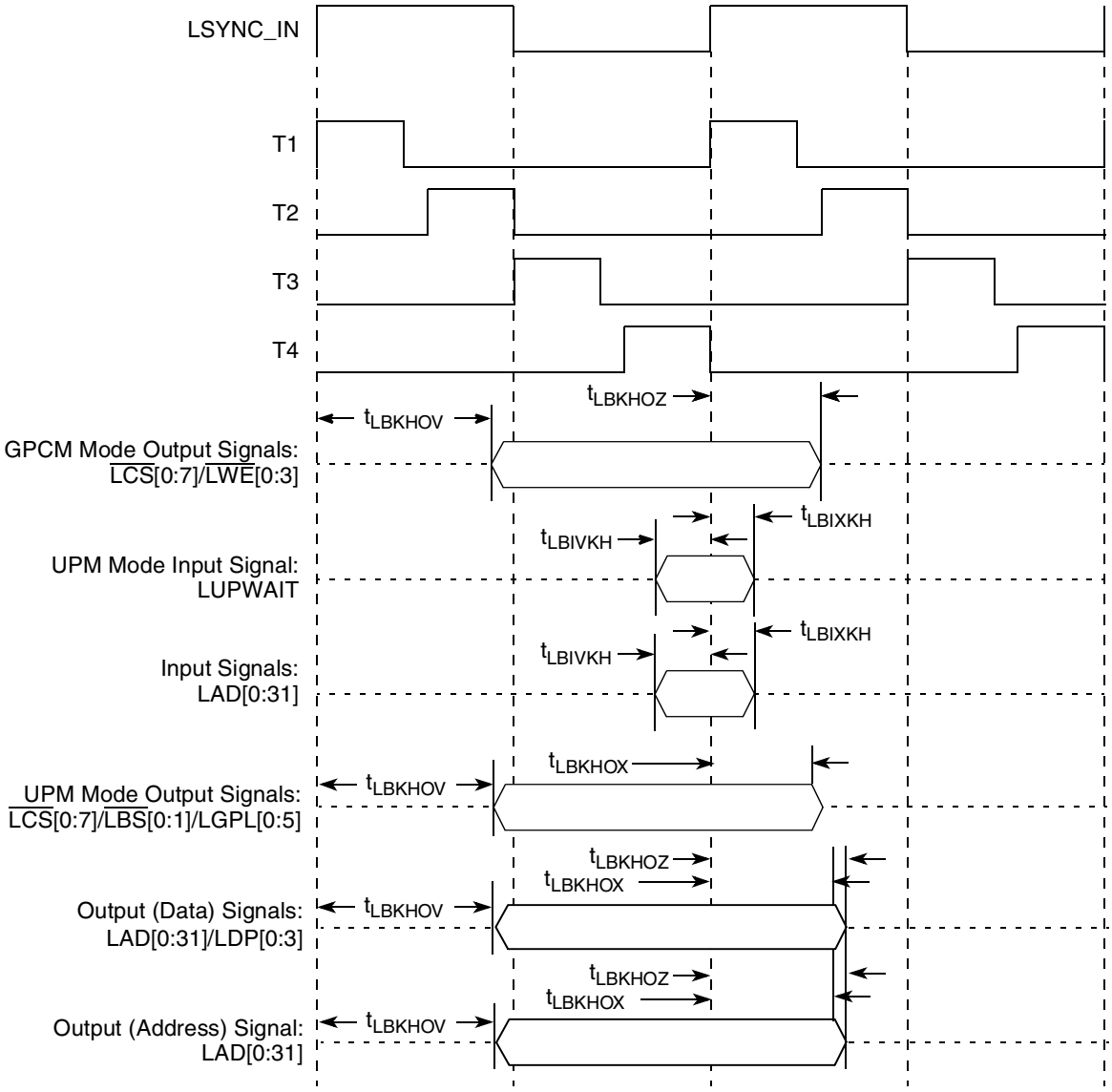


Figure 24. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4 (PLL Enable Mode)

Due to the special implementation of the eSDHC, there are constraints regarding the clock and data signals propagation delay on the user board. The constraints are for minimum and maximum delays, as well as skew between the CLK and DAT/CMD signals.

In full speed mode, there is no need to add special delay on the data or clock signals. The user should make sure to meet the timing requirements as described further within this document.

If the system is designed to support both high-speed and full-speed cards, the high-speed constraints should be fulfilled. If the systems is designed to operate up to 25 MHz only, full-speed mode is recommended.

11.1 eSDHC DC Electrical Characteristics

This table provides the DC electrical characteristics for the eSDHC (SD/MMC) interface of the device.

Table 41. eSDHC interface DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	$0.625 \times OV_{DD}$	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	–0.3	$0.25 \times OV_{DD}$	V
Input current	I_{IN}	—	—	±30	μA
Output high voltage	V_{OH}	I_{OH} = –100 uA, at OV_{DD}(min)	$0.75 \times OV_{DD}$	—	V
Output low voltage	V_{OL}	I_{OL} = +100 uA, at OV_{DD}(min)	—	$0.125 \times OV_{DD}$	V

11.2 eSDHC AC Timing Specifications (Full-Speed Mode)

This section describes the AC electrical specifications for the eSDHC (SD/MMC) interface of the device. This table provides the eSDHC AC timing specifications for full-speed mode as defined in Figure 27 and Figure 28.

Table 42. eSDHC AC Timing Specifications for Full-Speed Mode

At recommended operating conditions OV_{DD} = 3.3 V ± 165 mV.

Parameter	Symbol[1]	Min	Max	Unit	Note
SD_CLK clock frequency—full speed mode	f_{SFSCK}	0	25	MHz	—
SD_CLK clock cycle	t_{SFSCK}	40	—	ns	—
SD_CLK clock frequency—identification mode	f_{SIDCK}	0	400	KHz	—
SD_CLK clock low time	t_{SFSCKL}	15	—	ns	2
SD_CLK clock high time	t_{SFSCKH}	15	—	ns	2
SD_CLK clock rise and fall times	t_{SFSCKR}/ t_{SFSCKF}	—	5	ns	2
Input setup times: SD_CMD, SD_DATx, SD_CD to SD_CLK	$t_{SFSIVKH}$	5	—	ns	2

Table 45. JTAG AC Timing Specifications (Independent of CLKIN) [1] (continued)

Parameter	Symbol[2]	Min	Max	Unit	Note
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 2 2	 19 9	ns	5

Notes:
1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50 Ω load (see Figure 17). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.

This figure provides the AC test load for TDO and the boundary-scan outputs of the device.

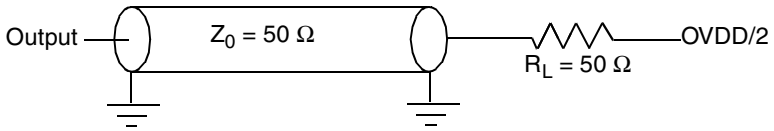


Figure 32. AC Test Load for the JTAG Interface

This figure provides the JTAG clock input timing diagram.

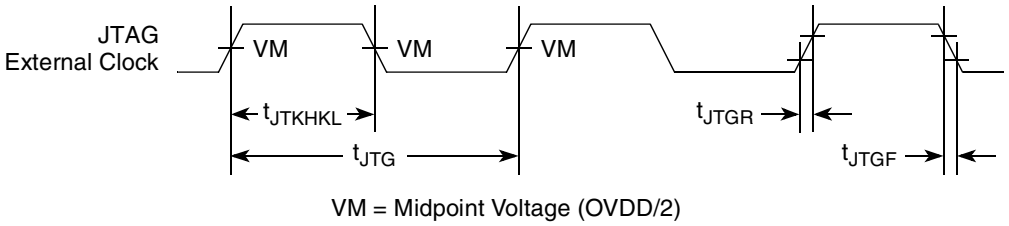


Figure 33. JTAG Clock Input Timing Diagram

This figure provides the $\overline{\text{TRST}}$ timing diagram.

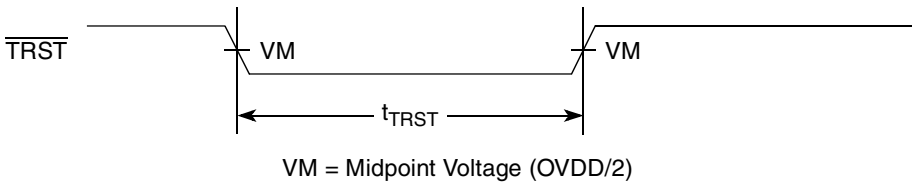


Figure 34. $\overline{\text{TRST}}$ Timing Diagram

18 GPIO

This section describes the DC and AC electrical specifications for the GPIO of the chip.

18.1 GPIO DC Electrical Characteristics

This table provides the DC electrical characteristics for the device GPIO.

Table 65. GPIO DC Electrical Characteristics

This specification applies when operating at 3.3 V ± 165 mV supply.

Parameter	Condition	Symbol	Min	Max	Unit
Output high voltage	I_{OH} = –6.0 mA	V_{OH}	2.4	—	V
Output low voltage	I_{OL} = 6.0 mA	V_{OL}	—	0.5	V
Output low voltage	I_{OL} = 3.2 mA	V_{OL}	—	0.4	V
Input high voltage	—	V_{IH}	2.0	OV_{DD} + 0.3	V
Input low voltage	—	V_{IL}	–0.3	0.8	V
Input current	0 V ≤ V_{IN} ≤ OV_{DD}	I_{IN}	—	± 30	μA

18.2 GPIO AC Timing Specifications

This table provides the GPIO input and output AC timing specifications.

Table 66. GPIO Input AC Timing Specifications

Parameter	Symbol	Min	Unit
GPIO inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of SYS_CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation.

This figure provides the AC test load for the GPIO.

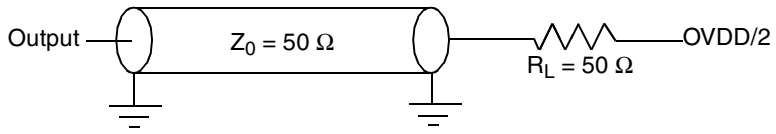


Figure 47. GPIO AC Test Load

19 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins of the chip.

Table 72. TePBGA II Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
MBA2	M3	O	GVDD	—
MCAS_B	W5	O	GVDD	—
MCK_B0	H1	O	GVDD	—
MCK_B1	K1	O	GVDD	—
MCK_B2	V1	O	GVDD	—
MCK_B3	W2	O	GVDD	—
MCK_B4	AA1	O	GVDD	—
MCK_B5	AB2	O	GVDD	—
MCK0	J1	O	GVDD	—
MCK1	L1	O	GVDD	—
MCK2	V2	O	GVDD	—
MCK3	W1	O	GVDD	—
MCK4	Y1	O	GVDD	—
MCK5	AB1	O	GVDD	—
MCKE0	M4	O	GVDD	3
MCKE1	R5	O	GVDD	3
MCS_B0	W3	O	GVDD	—
MCS_B1	P3	O	GVDD	—
MCS_B2	T4	O	GVDD	—
MCS_B3	R4	O	GVDD	—
MDIC0	AH8	I/O	GVDD	9
MDIC1	AJ8	I/O	GVDD	9
MDM0	B6	O	GVDD	—
MDM1	B2	O	GVDD	—
MDM2	E2	O	GVDD	—
MDM3	E1	O	GVDD	—
MDM4	Y6	O	GVDD	—
MDM5	AC6	O	GVDD	—
MDM6	AE6	O	GVDD	—
MDM7	AJ4	O	GVDD	—
MDM8	L6	O	GVDD	—
MDQ0	A8	I/O	GVDD	11
MDQ1	A6	I/O	GVDD	11

Table 72. TePBGA II Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
TSEC2_RXD0/GPIO1[16]	AE28	I/O	LVDD2	16
TSEC2_RXD1/GPIO1[15]	AE29	I/O	LVDD2	16
TSEC2_RXD2/GPIO1[14]	AH26	I/O	LVDD2	16
TSEC2_RXD3/GPIO1[13]	AH25	I/O	LVDD2	16
TSEC2_TX_CLK/GPIO2[24]/ TSEC1_TMR_GCLK	AG28	I/O	LVDD2	16
TSEC2_TX_EN/GPIO1[12]/ TSEC1_TMR_ALARM2	AJ26	I/O	LVDD2	16
TSEC2_TX_ER/GPIO1[24]/ TSEC1_TMR_ALARM1	AG26	I/O	LVDD2	16
TSEC2_TXD0/GPIO1[20]	AH28	I/O	LVDD2	16
TSEC2_TXD1/GPIO1[19]/ TSEC1_TMR_PP1	AF27	I/O	LVDD2	16
TSEC2_TXD2/GPIO1[18]/ TSEC1_TMR_PP2	AJ28	I/O	LVDD2	16
TSEC2_TXD3/GPIO1[17]/ TSEC1_TMR_PP3	AF29	I/O	LVDD2	16
GPIO1 Interface				
GPIO1[0]/GTM1_TIN1/ GTM2_TIN2/DREQ0_B	P25	I/O	OVDD	—
GPIO1[1]/GTM1_TGATE1_B/ GTM2_TGATE2_B/DACK0_B	N25	I/O	OVDD	—
GPIO1[2]/GTM1_TOUT1_B/ DDONE0_B	N26	I/O	OVDD	—
GPIO1[3]/GTM1_TIN2/ GTM2_TIN1/DREQ1_B	B9	I/O	OVDD	—
GPIO1[4]/GTM1_TGATE2_B/ GTM2_TGATE1_B/DACK1_B	N29	I/O	OVDD	—
GPIO1[5]/GTM1_TOUT2_B/ GTM2_TOUT1_B/DDONE1_B	M29	I/O	OVDD	—
GPIO1[6]/GTM1_TIN3/ GTM2_TIN4/DREQ2_B	A9	I/O	OVDD	—
GPIO1[7]/GTM1_TGATE3_B/ GTM2_TGATE4_B/DACK2_B	B10	I/O	OVDD	—
GPIO1[8]/GTM1_TOUT3_B/ DDONE2_B	J26	I/O	OVDD	—
GPIO1[9]/GTM1_TIN4/ GTM2_TIN3/DREQ3_B	J24	I/O	OVDD	—

Table 72. TePBGA II Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
GPIO1[10]/GTM1_TGATE4_B/ GTM2_TGATE3_B/DACK3_B	J27	I/O	OVDD	—
GPIO1[11]/GTM1_TOUT4_B/ GTM2_TOUT3_B/DDONE3_B	P24	I/O	OVDD	—
USB/GPIO2 Interface				
USBDR_CLK/GPIO2[23]	AJ11	I/O	OVDD	—
USBDR_DIR_DPPULLUP/ GPIO2[9]	AG12	I/O	OVDD	—
USBDR_NXT/GPIO2[8]	AJ10	I/O	OVDD	—
USBDR_PCTL0/GPIO2[11]/ SD_DAT2	AF10	I/O	OVDD	—
USBDR_PCTL1/GPIO2[22]/ SD_DAT3	AE9	I/O	OVDD	—
USBDR_PWRFAULT/ GPIO2[10]/SD_DAT1	AG13	I/O	OVDD	—
USBDR_STP_SUSPEND	AH12	O	OVDD	12
USBDR_D0_ENABLEN/ GPIO2[0]	AG10	I/O	OVDD	—
USBDR_D1_SER_TXD/ GPIO2[1]	AF13	I/O	OVDD	—
USBDR_D2_VMO_SE0/ GPIO2[2]	AG11	I/O	OVDD	—
USBDR_D3_SPEED/GPIO2[3]	AH11	I/O	OVDD	—
USBDR_D4_DP/GPIO2[4]	AG9	I/O	OVDD	—
USBDR_D5_DM/GPIO2[5]	AF9	I/O	OVDD	—
USBDR_D6_SER_RCV/ GPIO2[6]	AH13	I/O	OVDD	—
USBDR_D7_DRVVBUS/ GPIO2[7]	AH10	I/O	OVDD	—
I^2C Interface				
IIC1_SCL	C12	I/O	OVDD	2
IIC1_SDA	B12	I/O	OVDD	2
IIC2_SCL	A10	I/O	OVDD	2
IIC2_SDA	A12	I/O	OVDD	2
JTAG Interface				
TCK	B13	I	OVDD	—

Table 79. e300 Core PLL Configuration (continued)

RCWLR[COREPLL]			*core_clk* : *csb_clk* Ratio	VCO Divider [1]
0–1	2–5	6		
01	**0001**	1	1.5:1	4
10	**0001**	1	1.5:1	8
00	**0010**	0	2:1	2
01	**0010**	0	2:1	4
10	**0010**	0	2:1	8
00	**0010**	1	2.5:1	2
01	**0010**	1	2.5:1	4
10	**0010**	1	2.5:1	8
00	**0011**	0	3:1	2
01	**0011**	0	3:1	4
10	**0011**	0	3:1	8
00	**0011**	1	3.5:1	2
01	**0011**	1	3.5:1	4
10	**0011**	1	3.5:1	8
00	**0100**	0	4:1	2
01	**0100**	0	4:1	4
10	**0100**	0	4:1	8

Notes:
1. Core VCO frequency = Core frequency × VCO divider. Note that VCO divider has to be set properly so that the core VCO frequency is in the range of 800–1600 MHz.

23.3 Suggested PLL Configurations

This table shows suggested PLL configurations for different input clocks (LBCM = 0).

Table 80. Example Clock Frequency Combinations

								eLBC [1]			e300 Core [1]				
Ref [1]	**LBCM**	**DDRCM**	**SVCOD**	**SPMF**	**Sys VCO[1,2]**	**CSB[1,3]**	**DDR data rate[1,4]**	**/2**	**/4**	**/8**	**× 1**	**× 1.5**	**× 2**	**× 2.5**	**× 3**
25.0	0	1	2	5	500	125	250	62.5	31.3	15.6	—	—	—	—	375
25.0	0	1	2	6	600	150	300	75 [6]	37.5	18.8	—	—	—	375	450
33.3	0	1	2	5	667	167	333	83.3 [6]	41.6	20.8	—	—	333	416	500
33.3	0	1	2	4	533	133	267	66.7	33.3	16.7	—	—	—	333	400

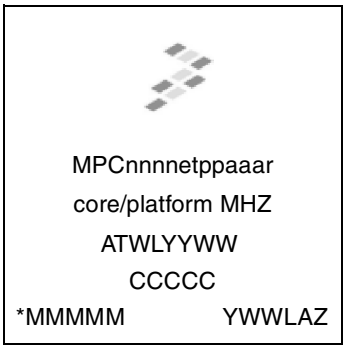
This table shows the SVR and PVR settings by device.

Table 86. SVR and PVR Settings by Product Revision

Device	Package	SVR		PVR	
		Rev 1.0	Rev. 2.1	Rev. 1.0	Rev. 2.1
MPC8377	TePBGA II	0x80C7_0010	0x80C7_0021	0x8086_1010	0x8086_1011
MPC8377E		0x80C6_0010	0x80C6_0021		
MPC8378		0x80C5_0010	0x80C5_0021		
MPC8378E		0x80C4_0010	0x80C4_0021		
MPC8379		0x80C3_0010	0x80C3_0021		
MPC8379E		0x80C2_0010	0x80C2_0021		

26.2 Part Marking

Parts are marked as in the example as shown in this figure.



TePBGA II

Notes:
ATWLYYWW is the traceability code.
CCCCC is the country code.
MMMMM is the mask number.
YWWLAZ is the assembly traceability code.

Figure 67. Freescale Part Marking for TePBGA II Devices

27 Document Revision History

This table provides a revision history for this document.

Table 87. Document Revision History

Revision	Date	Substantive Change(s)
8	05/2012	In Table 15, “DDR SDRAM DC Electrical Characteristics for GV_{DD} (typ) = 2.5 V,” updated Output leakage current (I_{OZ}) min and max values.
7	10/2011	• In Table 84, “Part Numbering Nomenclature,” updated “Revision Level description”and added footnote 4.In Section 21.2.4, “AC Requirements for SerDes Reference Clocks,” modified the introductory sentence for Table 71, “SerDes Reference Clock Common AC Parameters.”